

DEFORMATION POTENTIAL CONSTANTS  $\Xi_u$   
AND  $\Xi_d$  IN  $n$ -Si DETERMINED WITH THE USE  
OF THE TENSORESISTANCE EFFECT

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S u m m a r y

On the basis of longitudinal piezoresistance measurements in the geometry  $X \parallel J \parallel [100]$  and the theory of anisotropic scattering, the deformation potential constants  $\Xi_u$  and  $\Xi_d$  for  $\gamma$ -irradiated  $n$ -Si have been determined. It has been shown that, while determining the anisotropy of relaxation times for  $n$ -Si with the deep energy level  $E_c - 0.17$  eV, the dependence of the concentration of deep ionized centers on the deformation must be taken into consideration.